



PATENT ABSTRACTS OF JAPAN

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H01L 29/786**G02F 1/1368****G09F 9/30****H01L 21/20****H01L 21/28**(21) Application number: **2000213560**(71) Applicant: **SONY CORP**(22) Date of filing: **14.07.00**(72) Inventor: **HAYASHI HISAO**(54) **THIN-FILM SEMICONDUCTOR DEVICE**

(57) Abstract:

PROBLEM TO BE SOLVED: To rationalize the production process of a thin-film dual-gate transistor.

SOLUTION: The thin-film semiconductor device contains at least the thin-film transistor formed on a substrate 1. The transistor has the dual-gate structure which is composed of a semiconductor thin film 4 and a pair of gate electrodes 2F, 2R which are arranged in the upper part and the lower part of the film 4 via respective insulating films. The gate electrode 2R on one side is composed of a material whose transmissivity is at less than 1%. The gate electrode 2F on the other side is composed of a material whose transmissivity is at 1% or more.

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